

## FDC6312P

### Dual P-Channel 1.8V PowerTrench® Specified MOSFET

#### General Description

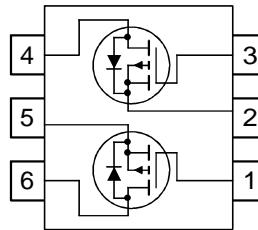
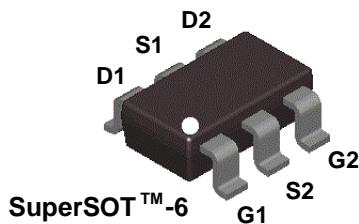
These P-Channel 1.8V specified MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

#### Applications

- Power management
- Load switch

#### Features

- -2.3 A, -20 V.  $R_{DS(ON)} = 115 \text{ m}\Omega$  @  $V_{GS} = -4.5 \text{ V}$   
 $R_{DS(ON)} = 155 \text{ m}\Omega$  @  $V_{GS} = -2.5 \text{ V}$   
 $R_{DS(ON)} = 225 \text{ m}\Omega$  @  $V_{GS} = -1.8 \text{ V}$
- High performance trench technology for extremely low  $R_{DS(ON)}$
- SuperSOT™-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick)



#### Absolute Maximum Ratings

$T_A=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	-20	V
$V_{GSS}$	Gate-Source Voltage	$\pm 8$	V
$I_D$	Drain Current – Continuous	-2.3	A
	– Pulsed	-7	
$P_D$	Power Dissipation for Single Operation	0.96	W
		0.9	
		0.7	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

#### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	130	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	60	$^\circ\text{C}/\text{W}$

#### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.312	FDC6312P	13"	12mm	3000 units

## Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}} = 0 \text{ V}$ , $I_D = -250 \mu\text{A}$	-20			V
$\frac{\Delta \text{BV}_{\text{DSS}}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-11		$\text{mV}^\circ\text{C}$
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{\text{DS}} = -16 \text{ V}$ , $V_{\text{GS}} = 0 \text{ V}$		-1		$\mu\text{A}$
$I_{\text{GSSF}}$	Gate-Body Leakage, Forward	$V_{\text{GS}} = 8 \text{ V}$ , $V_{\text{DS}} = 0 \text{ V}$		100		nA
$I_{\text{GSSR}}$	Gate-Body Leakage, Reverse	$V_{\text{GS}} = -8 \text{ V}$ , $V_{\text{DS}} = 0 \text{ V}$		-100		nA

### On Characteristics (Note 2)

$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}$ , $I_D = -250 \mu\text{A}$	-0.4	-0.9	-1.5	V
$\frac{\Delta V_{\text{GS(th)}}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$ , Referenced to $25^\circ\text{C}$		2		$\text{mV}^\circ\text{C}$
$R_{\text{DS(on)}}$	Static Drain-Source On-Resistance	$V_{\text{GS}} = -4.5 \text{ V}$ , $I_D = -2.3 \text{ A}$ $V_{\text{GS}} = -2.5 \text{ V}$ , $I_D = -1.9 \text{ A}$ $V_{\text{GS}} = -1.8 \text{ V}$ , $I_D = -1.6 \text{ A}$ $V_{\text{GS}} = -4.5 \text{ V}$ , $I_D = -2.3 \text{ A}$ , $T_J = 125^\circ\text{C}$		92 116 166 112	115 155 225 150	$\text{m}\Omega$
$I_{\text{D(on)}}$	On-State Drain Current	$V_{\text{GS}} = -4.5 \text{ V}$ , $V_{\text{DS}} = -5 \text{ V}$	-7			A
$g_{\text{FS}}$	Forward Transconductance	$V_{\text{DS}} = -5 \text{ V}$ , $I_D = -3.5 \text{ A}$		5.3		S

### Dynamic Characteristics

$C_{\text{iss}}$	Input Capacitance	$V_{\text{DS}} = -10 \text{ V}$ , $V_{\text{GS}} = 0 \text{ V}$ , $f = 1.0 \text{ MHz}$		467		pF
$C_{\text{oss}}$	Output Capacitance			85		pF
$C_{\text{rss}}$	Reverse Transfer Capacitance			38		pF

### Switching Characteristics (Note 2)

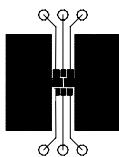
$t_{\text{d(on)}}$	Turn-On Delay Time	$V_{\text{DD}} = -10 \text{ V}$ , $I_D = -1 \text{ A}$ ,		8	16	ns
$t_r$	Turn-On Rise Time	$V_{\text{GS}} = -4.5 \text{ V}$ , $R_{\text{GEN}} = 6 \Omega$		13	23	ns
$t_{\text{d(off)}}$	Turn-Off Delay Time			18	32	ns
$t_f$	Turn-Off Fall Time			8	16	ns
$Q_g$	Total Gate Charge	$V_{\text{DS}} = -10 \text{ V}$ , $I_D = -2.3 \text{ A}$ ,		4.4	7	nC
$Q_{\text{gs}}$	Gate-Source Charge	$V_{\text{GS}} = -4.5 \text{ V}$		1.0		nC
$Q_{\text{gd}}$	Gate-Drain Charge			0.8		nC

### Drain-Source Diode Characteristics and Maximum Ratings

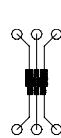
$I_S$	Maximum Continuous Drain-Source Diode Forward Current			-0.8		A
$V_{\text{SD}}$	Drain-Source Diode Forward Voltage	$V_{\text{GS}} = 0 \text{ V}$ , $I_S = -0.8 \text{ A}$ (Note 2)		-0.7	-1.2	V

#### Notes:

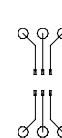
- $R_{\text{thJA}}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\text{thJC}}$  is guaranteed by design while  $R_{\text{thCA}}$  is determined by the user's board design.



a)  $130^\circ\text{C/W}$  when mounted on a  $0.125 \text{ in}^2$  pad of 2 oz. copper.



b)  $140^\circ\text{C/W}$  when mounted on a  $0.004 \text{ in}^2$  pad of 2 oz copper



c)  $180^\circ\text{C/W}$  when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width  $< 300\mu\text{s}$ , Duty Cycle  $< 2.0\%$

## Typical Characteristics

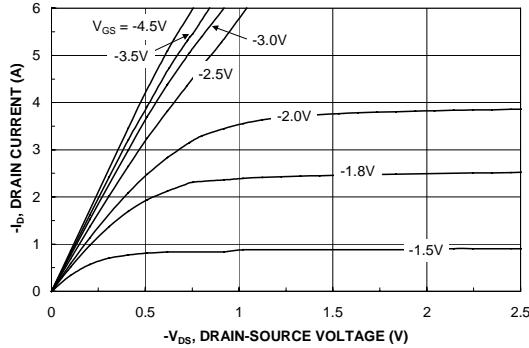


Figure 1. On-Region Characteristics.

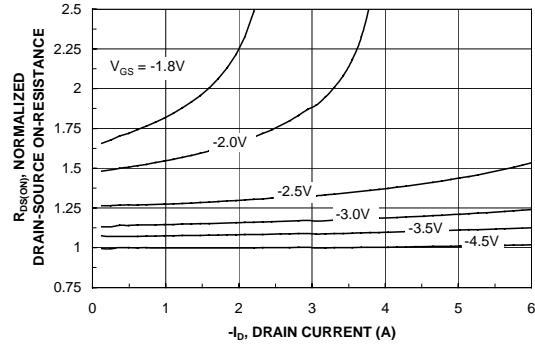


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

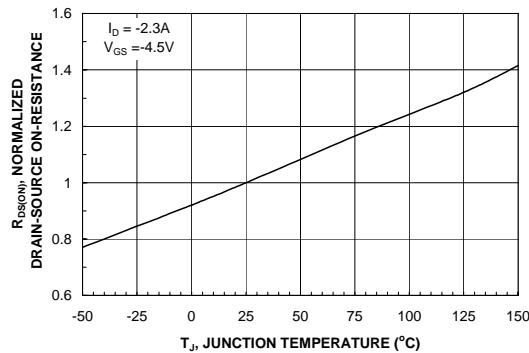


Figure 3. On-Resistance Variation with Temperature.

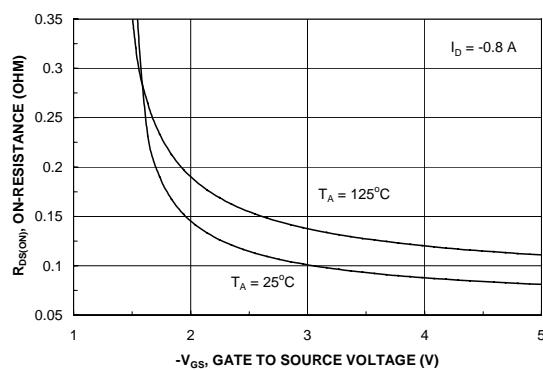


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

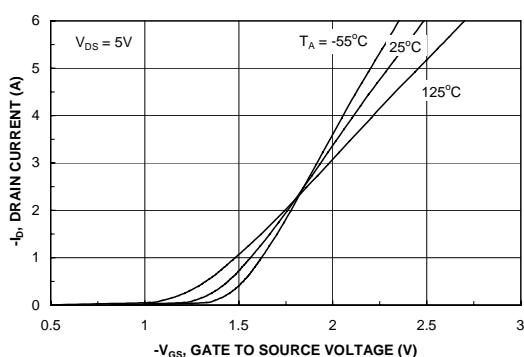


Figure 5. Transfer Characteristics.

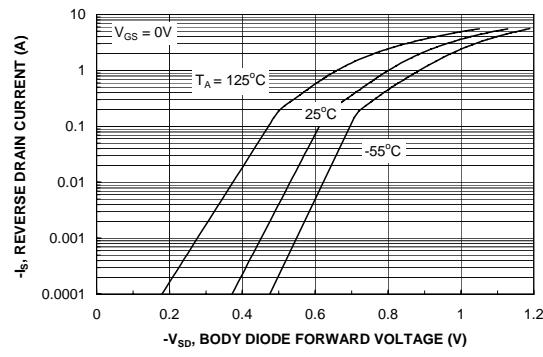


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## Typical Characteristics

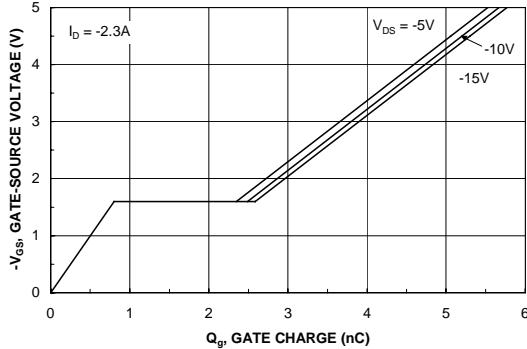


Figure 7. Gate Charge Characteristics.

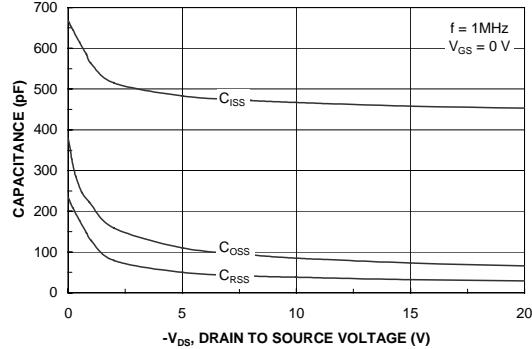


Figure 8. Capacitance Characteristics.

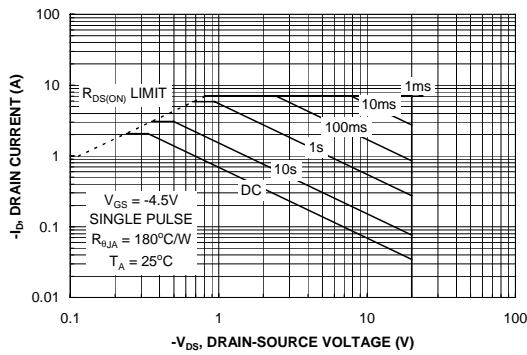


Figure 9. Maximum Safe Operating Area.

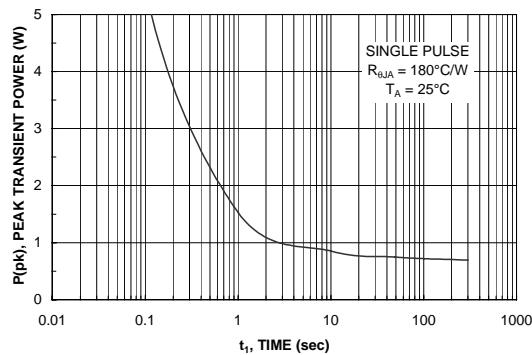


Figure 10. Single Pulse Maximum Power Dissipation.

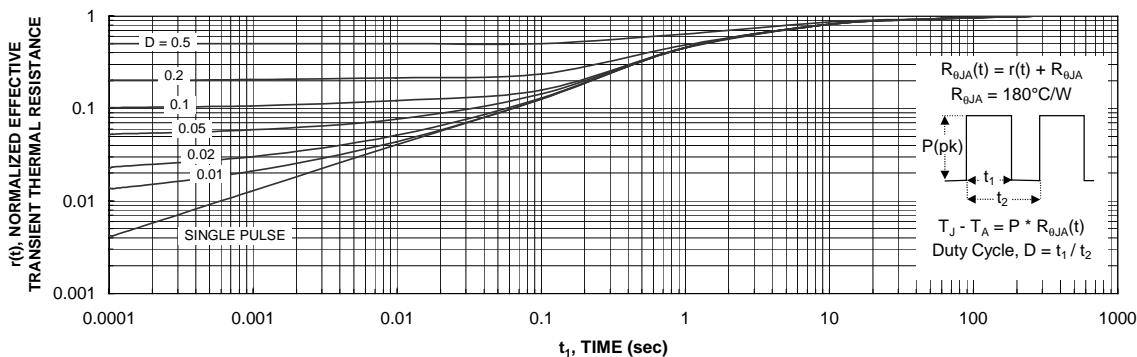


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.  
Transient thermal response will change depending on the circuit board design.

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